Vishay Siliconix

# N-Channel 60 V (D-S) MOSFET

### **DESCRIPTION**

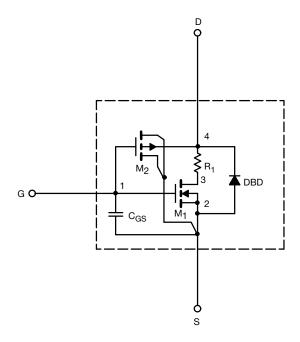
The attached SPICE model describes the typical electrical characteristics of the n-channel vertical DMOS. The sub-circuit model is extracted and optimized over the -55  $^{\circ}\text{C}$  to +125  $^{\circ}\text{C}$  temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched  $C_{gd}$  model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

### **CHARACTERISTICS**

- N-Channel Vertical DMOS
- Macro Model (Sub-circuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the -55 °C to +125 °C Temperature Range
- · Model the Gate Charge

### SUBCIRCUIT MODEL SCHEMATIC



### Note

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer
to the appropriate datasheet of the same number for guaranteed specification limits.



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| SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted) |                     |   |                |                  |      |
|---|---------------------|---|----------------|------------------|------|
| PARAMETER   | SYMBOL              | TEST CONDITIONS   | SIMULATED DATA | MEASURED<br>DATA | UNIT |
| Static  |                     |   |                |                  |      |
| Gate Threshold Voltage  | V <sub>GS(th)</sub> | $V_{DS} = V_{GS}$ , $I_D = 250 \mu A$                                   | 1.6            | -                | V    |
| On-State Drain Current <sup>a</sup>                             | I <sub>D(on)</sub>  | $V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$                           | 4              | -                | Α    |
| Drain-Source On-State Resistance a                              | R <sub>DS(on)</sub> | $V_{GS} = 10 \text{ V}, I_D = 500 \text{ mA}$                           | 1.1            | 1.1              | Ω    |
|   |                     | $V_{GS} = 4.5 \text{ V}, I_D = 200 \text{ mA}$                          | 1.6            | 1.6              |      |
| Forward Transconductance <sup>a</sup>                           | 9 <sub>fs</sub>     | $V_{DS} = 10 \text{ V}, I_D = 200 \text{ mA}$                           | 240            | 550              | S    |
| Diode Forward Voltage <sup>a</sup>                              | V <sub>SD</sub>     | $I_S = 200 \text{ mA}, V_{GS} = 0 \text{ V}$                            | 0.85           | 0.87             | V    |
| Dynamic <sup>b</sup>  |                     |   |                |                  |      |
| Total Gate Charge   | $Q_g$               | $V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 250 \text{ mA}$ | 0.30           | 0.40             | nC   |
| Gate-Source Charge  | Q <sub>gs</sub>     |   | 0.11           | 0.11             |      |
| Gate-Drain Charge   | $Q_{gd}$            |   | 0.15           | 0.15             |      |

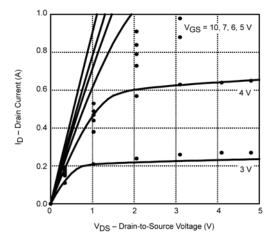
### Notes

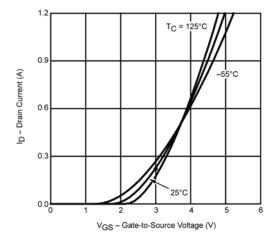
- a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.

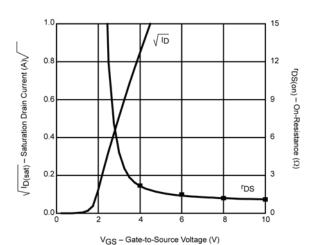
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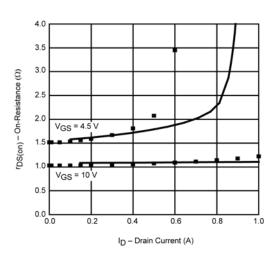
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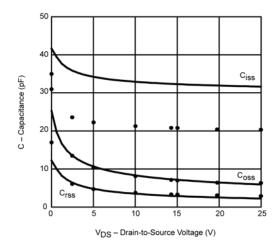
### **COMPARISON OF MODEL WITH MEASURED DATA** ( $T_J = 25~^{\circ}C$ , unless otherwise noted)

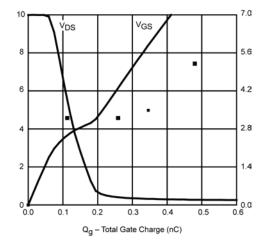












#### Note

Dots and squares represent measured data.
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Revision: 02-Oct-12 Document Number: 91000